	L Number	Hits	Search Text	DB	Time stamp
	1	2322	cladding with buffer with layer	USPAT;	2004/05/05
			cradding with burier with rayer	•	
				US-PGPUB;	13:46
	`	·,		EPO; JPO;	1
.	,	1000		DERWENT	2004/05/05
1	2 .	1260	· · · · · · · · · · · · · · · · · · ·	USPAT;	2004/05/05
Į		· .	act\$3	US-PGPUB;	[ 13:47
-	,	, .		EPO; JPO;	(
1	•			DERWENT	:
{ :	3	257	(cladding with buffer with layer with	USPAT;	2004/05/05
	·	~	act\$3) and 438/\$3.ccls.	US-PGPUB;	13:47
		· ·		EPO; JPO;	
				DERWENT	
,	4	: 29	cladding with buffer with layer with (act	USPAT;	2004/05/05
-		]	or acting)	US-PGPUB;	13:54
}			;	EPO; JPO;	
1	·	•		DERWENT	
1	5 ,		form\$3 with superlattice with buffer with	USPAT;	2004/05/05
'			· <del>-</del>	US-PGPUB;	13:59
		•	(over or on) with (semiconductor or		13.39
1			gan")	EPO; JPO;	<b>\</b>
}	, · Ì		F02	DERWENT	2004/05/05
1	6	,5	form\$3 with grad\$3 with buffer with (over	USPAT;	2004/05/05
1			or on) with (semiconductor or "gan")	US-PGPUB;	15:03
				EPO; JPO;	(n)
	• 1	·		DERWENT	
}	7	. 6		USPAT; .	2004/05/05
}			(over or on) with (semiconductor or	US-PGPUB;	15:03
{			"gan")	EPO; JPO;	]
ŀ				DERWENT	ļ
	_	209	(fabricat\$3 with gan with substrate) and	USPAT;	2004/05/05
<b> </b> ' .	•	}	(crack or fault or defect)	US-PGPUB;	13:45
		}	102401 02 24420 02 4020007	EPO; JPO;	
}		·		DERWENT	
		117	[ [ fabricates with an with auhatantal and	USPAT;	2003/06/13
'		147		A .	
1	-	(	(crack or fault or defect)) and (buffer	US-PGPUB;	15:39
		,	with gan)	EPO; JPO;	
1			1,1,1,5,1,1,1,1,1,1,1,1,1,1,1,1,1,1,1,1	DERWENT	2002/00/22
1.		17		USPAT;	2003/06/13
1.		{	and (crack or fault or defect)) and	US-PGPUB;	15:42
`			(buffer with gan)) and ((buffer with	EPO; JPO;	
<b>.</b>			first) and (buffer with second))) and	DERWENT	
			@ad<20010305		1
} .	_	7.0	(sapphire with substrate) and (crack or	USPAT;	2003/0.6/13
1			fault or defect) and ((upper or second or	US-PGPUB;	16:46
,[			first) with buffer with gan) and (lower	EPO; JPO;	
1	e 19		with buffer with gan)	DERWENT	
.	_	36	((sapphire with substrate) and (crack or	USPAT;	2003/06/13
] .	•	<u> </u>	fault or defect) and ((upper or second or	US-PGPUB;	16:04
1			first) with buffer with gan) and (lower	EPO; JPO;	
	,		with buffer with gan)) and @ad<20010305	DERWENT	
	2	1	((sapphire with substrate) and (crack or	USPAT;	2003/06/13
		] <u>L</u>	,	US-PGPUB;	16:02
	•		fault or defect) and ((upper or second or		10.02
}			first) with buffer with gan) and (lower	EPO; JPO;	}
			with buffer with gan)) and (gan with	DERWENT	<b>{</b> `
			semiconductor with substrate with	·	
1	1		fabrication)	••••	0000155155
-	<b>-</b>	22		USPAT;	2003/06/13
		}	with fabrication	US-PGPUB;	16:04
1		<b>)</b> `` `		EPO; JPO;	
[		Į		DERWENT	<b>,</b>
-	-	15	(gan with semiconductor with substrate	USPAT;	2003/06/13
1			with fabrication) and @ad<20010305	US-PGPUB;	17:10
		[		EPO; JPO;	
1				DERWENT .	,
		1	(sapphire with substrate) and (crack or	USPAT;	2003/06/13
	• • • •	. 110	L CARLOTTE WITH SIDELIAND ASSESSMENT AND THE CONTRACTOR	(/, T = ·	
		118		· ·	
-		118.	fault or defect) and ((silicon with dop\$3	US-PGPUB;	16:48
_		118		· ·	

			<u>.                                    </u>				
	.]. —			3	((sapphire with substant)		•
•		.,			((sapphire with substrate) and (crack or	USPAT;	2003/06/13
	1				fault or defect) and ((silicon with dops)	A	; 18:42
,					$10^{\circ}$	EPO; JPO	. 120.42
٠.	.]		1		9am/// and (dichlorosilane or	DERWENT	′ ′
	·}		-	•	"sin.sub.2cl.sub.2")	DEVARIAT	
	ļ, <del>-</del> .		}	4	(gan with semiconductor with substants		
		`. <b>•</b>	ł		with fabrication) and ((sapphire with	USPAT;	2003/06/13
•					substrate) and (sappnire with	US-PGPUB	;   16:52
			[		substrate) and (crack or fault or defect)	EPO; JPO	;
	ļ		· ,		I alla 1 (SIIICON WITH dons ? rrith hiteen)	DERWENT	
* *	_	• .		י זר	1 (STITEOUT WITH GODS & WITH GOD) / (		
		1,	ł	35	1. ((Iabricat\$3 with dan with substants)	IICDAM	
			٠.	*	Tand (Clack of fault or defect))	USPAT;	2003/06/13
	1	•	ļ. ·	, , , ,	(buffer with gan)) and ((buffer with	US-PGPUB;	
		`. "		· .	first) and (buffer with second))	EPO; JPO;	
,	_			<u>"</u> 3	((sapphine with second))	DERWENT'	
	}·	: *	•	","	((sapphire with substrate) and (crack or	USPAT;	2,003/06/13
		ł	٠.		I raure or defect) and ((gilicon with deman		16:58
		}			With Duller   Of (S)   1 Con with done?	EPO; JPO;	
		- 1	·		yan, / / and (((labricats3 with and + -		- P
		- 1	•		Substitute   and (Crack or fault on	DERWENT	
		ł			defect)) and (buffer with gan)) and	; ,	7"
J		.		٠,	((buffer with first) and		
		1	•		((buffer with first) and (buffer with second)))		`
]	<b>-</b> , .			566	(harff		- 1 × 1
		- 1		5.00	(buffer with ((multi adj layer) or,	USPAT;	2002/06/12
· · ·	•	- 4			(multiple adj layer)))		2003/06/13
	•	- 4		Ì		US-PGPUB;	18:06
. 1				. '		EPO; JPO;	
	<del>-</del> ··" ·	٠ ٠ ]		5	((sapphire with substrate) and (crack or	DERWENT	
				- 1	fault or defeat) and (crack or	USPAT;	2003/06/13
. !	•	' ·			fault 'or defect) and ((silicon with dop\$3	US-PGPUB;	17:01
.[	A	[		.	with Duller) or (Silicon with dones with	EPO; JPO;	17:01
j		J		. · · /	.9911/// and ((Duller With (/miltinal	DERWENT	
· 4.	,			* ]	rayer) or (multiple adi laver))))	DEKAMEMI	
· [	; <del>-</del>			25	(buffer with ((multi adj layer) or	****	
					(multiple adj layer)) with dop\$3)	ÚSPÁT;	2003/06/13
	•	٠	·	[	Tayer) with dops3)	US-PGPUB;	17:10
		.		· · · · · · ·		EPO; JPO;	
0	_	-		19	1/2	DERWENT	
	,	·		. 19	((buffer with ((multi adj layer) or	· USPAT;	2002/06/12
- 1			٠.	· 1	(multiple ad] layer)) with dons3)) and		2003/06/13
- 1		•			@ad<20010305 and	US-PGPUB;	17:13
		·		.		EPO; JPO;	
.   '		-	>	2	(gan with semiconductor with substrate	DERWENT	
].					with fabrication)	USPAT;	2003/06/13
ļ.			•		with fabrication) and ((buffer with	US-PGPUB;	17:12
		- 1			((multi adj layer) or (multiple adj	EPO; JPO;	
	<u>.</u>	1.			layer))))	DERWENT	
1.				42	((buffer with ((multi adj layer) or	USPAT;	10000 (000 (00
,;		. [	,	*	(multiple adj layer)))) and gan and		2003/06/13
		•			sapphire	US-PGPUB;	17:13
		-		1		EPO; JPO;	
-		1	<b>.</b>	27	(((buffer with //miles	DERWENT	1
		- [	•		(((buffer with ((multi adj layer) or	USPAT;	2003/06/13
٠,	*;				(murciple ad] laver)))) and dan and	US-PGPUB;	18:57
* .	,	$\cdot \mid  \mid$		5	sapphire) and @ad<20010305	EPO; JPO;	1.10.07
.			٠ ,				
-	•	*	. : ` `	0   1	(buffer with ((multi adj layer) or	DERWENT	
}	. * * .	1	*4		multiple adj layer))) same gradient same	USPAT;	2003/06/13
		1				US-PGPUB;	17:58
	***	1			I i - / min yaii	EPO; JPO;	·
.   -		1.			· •	DERWENT	•. **
-		1	•	~   \	(butter same ([mi][t] add laver) on	USPAT;	2003/06/13
	•	1		\	multiple add laver))) same gradient same	US-PGPUB;	
-		1		-d			17:58
		1	•	.	·	EPO; JPO;	
,   <del>-</del>	,	1		0 (	ADULTE: Same (Immitte Sale less)	DERWENT	
ŀ				" 1 i	MULLIDIE ACT ISVONIII	USPAT;	2003/06/13
-   -			•	'	multiple adj layer))) same gradient) and	US-PGPUB;	17:59
1		1.		١٩		EPO; JPO;	
	., •	1		7 1		DERWENT	. · · ·
	11	1	-	` / [ b	MTTCT 30000 USU CSMV 44255	USPAT;	2002/06/25
.	0	ľ	<del>1</del>			•	2003/06/13
1		ł		ĺ		US-PGPUB;	18:05
	•	1		1		EPO; JPO;	
-		1	. 14	18 ()	ouffer same anadional	DERWENT	· .
				-   '	ANTIGE DAME (ILSUIDAL) JANA WAR	USPAT;	2003/06/13
	•	ļ		1			18:24
	1	₹.	•			EPO; JPO;	10.23
<u> </u>	<del></del>	L	<del>-</del>				
						DERWENT	
Coo		<del></del>	• 1		· ·		

					•
[	_ ,	1 0	((buffer with ((multi adj layer) or	USPAT;	2003/06/13
		{	(multiple adj layer)) with dop\$3)) and	US-PGPUB;	18:05
1	•		((buffer same gradient) and gan)	EPO; JPO;	
1		· ·	((Duller Same gradient) and gail)		Į t
1				DERWENT	
1	_	0	((buffer with ((multi adj layer) or	USPAT;	2003/06/13
- [		1	(multiple adj layer)))) and ((buffer same	US-PGPUB;	18:05
1	•		(gradient) and gan)	EPO; JPO;	
ļ				DERWENT	
j	_	3	(buffer with ((multi adj layer) or	USPAT;	2003/06/13
[	• .	, ,			1
ļ			(multiple adj layer))) and (buffer same	US-PGPUB;	18:23
ļ		İ	concentration same gradient)	EPO; JPO;	
4				DERWENT	
Į		213	buffer with layer with gradient	USPAT;	2003/06/13
Į				US-PGPUB;	18:49
ļ				EPO; JPO;	
ļ					· · · · · · · · · ·
ļ				DERWENT	ا مینی در در ا
ļ	-	12	(buffer with layer with gradient) and gan		2003/06/13
·		ļ.·		US-PGPUB;	18:49
┨		,		EPO; JPO;	
				DERWENT	{·
ļ	_	ξ.	buffer with (dichlorosilane or	USPAT;	2003/06/13
ļ					
1			"sih.sub.2cl.sub.2")	US-PGPUB;	18:43
.{		101		EPO; JPO;	
, {	•			DERWENT	<b>,</b>
• {	*	531	(buffer with layer) same gradient	USPAT;	2003/06/13
1			}	US-PGPUB;	18:49
-			<b>\</b>	EPO; JPO;	
-					1
}				DERWENT	
}	-	22	((buffer with layer) same gradient) and	USPAT;	2003/06/13
}		1.	gan	US-PGPUB;	1.18:57
. }	•	· · ·		EPO; JPO;	
ł		· · · · · · ·		DERWENT	}
-		209	super with lattice with dop\$3	USPAT;	2003/06/13
1		,	buper with raceree with depts	US-PGPUB;	18:57
1					10.3/
[.	•			EPO; JPO;	
)				DERWENT	
)	-	19	(super with lattice with dop\$3) same gan	USPAT;	2003/06/13
1				US-PGPUB;	18:57
1				EPO; JPO;	1/5,
1				DERWENT	}
1	_	12	((super with lattice with dop\$3) same	USPAT;	2003/06/13
ł			gan) and @ad<20010305	US-PGPUB;	19:09
ŀ			gail, and ead\20010303		119.09
i				EPO; JPO;	
ĺ	· •			DERWENT	
. [	-	10	(((super with lattice with dop\$3) same	USPAT;	2003/06/13
Į	·		gan) and @ad<20010305) and buffer	US-PGPUB;	19:07
. [	•	J	<b>{</b>	EPO; JPO;	
ij		,		DERWENT	
-	•	44	(first adj buffer) and (second adj	USPAT;	2003/06/13
1					
1	•	1	buffer) and concentration and symmetrical	US-PGPUB;	19:35
1		1		EPO; JPO;	
.{		<u> </u>		DERWENT	
1	- · ·	39	((first adj buffer) and (second adj	USPAT;	2003/06/13
. {		<b>1</b>	buffer) and concentration and	US-PGPUB;	20:09
1	•	1	symmetrical) and @ad<20010305	EPO; JPO;	}
[	• •	. •.		DERWENT	
1		181	(first adj buffer) and (second adj	USPAT;	2003/06/13
}	•	101			(
}			buffer) and concentration and gradient	US-PGPUB;	19:37
}		}	<b>}</b>	EPO; JPO;	}
}		}	<b>}</b>	DERWENT	j l
Ì	<b>_</b> '	22	((first ad) buffer) and (second ad)	USPAT;	2003/06/13
ŀ		}	buffer) and concentration and gradient)	US-PGPUB;	20:06
1			and (438/\$3.ccls. or 257/\$3.ccls.)	EPO; JPO;	
1	00		(	DERWENT	ALLE THE SECOND SECTION OF THE PROPERTY OF THE
	_	least to Force	(b) FFON 19 FB do 62 - 1 - 1		2002/05/12
	, - ,	526	(buffer with dop\$3 with concentration)	USPAT;	2003/06/13
		1	and (438/\$3.ccls. or 257/\$3.ccls.)	US-PGPUB;	20:21
,			<u> </u>	EPO; JPO;	]
		[		DERWENT	
	-	66	((buffer with dop\$3 with concentration)	USPAT;	2003/06/13
		.: "	and (438/\$3.ccls. or 257/\$3.ccls.)) and	US-PGPUB;	20:08
- 1			(buffer with multi\$3)	,	[ 20.,00.
[			/MATTET ATOM MATCT39	EPO; JPO;	
{				DERWENT	l .· ·

<u> </u>		<u>`</u>		
-	66	((buffer with dop\$3 with concentration)	USPAT;	2003/06/13
*	ļ	and (438/\$3.ccls. or 257/\$3.ccls.)) and	US-PGPUB;	20:21
	{ <u>,</u> .	(buffer with multi\$3 with layer)	EPO; JPO;	
		(2011-11-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-	DERWENT	
	53	///buffer with dence with concentration)	USPAT;	2003/06/13
1.	33		,	,
	<b>\</b>	and (438/\$3.ccls. or 257/\$3.ccls.)) and	US-PGPUB;	20:52
	{ .	(buffer with multi\$3 with layer)) and	EPO; JPO;	
•	·	@ad<20010305	DERWENT	
	89	method with fabricat\$3 with gan with	USPAT;	2003/06/13
		substrate	US-PGPUB;	20:16
•	<b>[</b>	Subscrace	•	20.10
	<b>∫</b> . •		EPO; JPO;	
	}		DERWENT	
<b>↓</b> :~	5	((buffer with dop\$3 with concentration)	USPAT;	2003/06/13
\ \ , .	} .	and (438/\$3.ccls. or 257/\$3.ccls.)) and	US-PGPUB;	20:16
·	}	(method with fabricat\$3 with gan with	EPO; JPO;	
,	} '-	substrate)	DERWENT	<u>'</u>
	12	•	USPAT;	2003/06/13
	}	same (buffer with multiple with layer)	US-PGPUB;	20:39
		same (butter with muttiple with tayer)	· ·	20.39
			EPO; JPO;	
] • [	]		DERWENT	
] = 1	0	(buffer with dop\$3 with profile) same	USPAT;	2003/06/13
] : ;	]	(buffer with multiple with layer)	US-PGPUB;	20:38
].			EPO; JPO;	
1	]		DERWENT	
Į_ ·· [		(buffer with increas\$3 with	USPAT;	2003/06/13
	2		,	
Į į	<b>!</b>	concentration) same (buffer with multiple	US-PGPUB;	20:40
	[ · · ·	(with layer)	EPO; JPO;	
	Į		DERWENT	
( - ·	4	(buffer with increas\$3 with dop\$3) same	USPAT;	2003/06/13
		(buffer with multiple with layer)	US-PGPUB;	20:42
		(baller witter martiple witter rayer)	EPO; JPO;	1.201.12
	<b>[</b>			
			DERWENT	
( -		buffer with doping with concentration	USPAT;	2003/06/13
		with profile ,	US-PGPUB;	20:45
			EPO; JPO;	
,			DERWENT	• • •
\ <u></u>	14	buffer with dop\$3 with gradient	USPAT;	2003/06/13
	}	Saller wrom dopped wrom gradient	US-PGPUB;	20:51
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	, .			20.31
. ,			EPO; JPO;	
			DERWENT	
-	826	buffer with dop\$3 with concentration	USPAT;	2003/06/13
			US-PGPUB;	20:52
	·		EPO; JPO;	
			DERWENT	
	165	(buffer with dop\$3 with concentration)	USPAT;	2003/06/13
• • •	105	_		1
j	· ·	and gan	US-PGPUB;	20:52
<u> </u>	<b>}</b> .		EPO; JPO;	
1 .	}		DERWENT	· · _ ·
) -	. 45	((buffer with dop\$3 with concentration)	USPAT;	2003/06/13
		and gan) and 438/\$3.ccls.	US-PGPUB;	21:09
			EPO; JPO;	*
	[		DERWENT .	
1_	31	(((buffer with dop\$3 with concentration)	USPAT;	2003/06/13
Į.	31	_ · · · · · · · · · · · · · · · · · · ·		
	[	and gan) and 438/\$3.ccls.) and	US-PGPUB;	21:09
	[	@ad<20010305	EPO; JPO;	
			DERWENT	
\ <b>-</b>	89	buffer with doped with undoped with gan	USPAT;	2003/06/13
, · .			US-PGPUB;	21:09
(		· .	EPO; JPO;	
	,		DERWENT .	
1,		/byffan vitek damed eitek innden a eitek kinne		2002/06/12
( - · · · )	61	(buffer with doped with undoped with gan)	USPAT;	2003/06/13
1		and @ad<20010305	US-PGPUB;	21:09
· · · · ·		·	EPO; JPO;	
,			DERWENT	A STATE OF THE STA
	13	((buffer with doped with undoped with	USPAT;	2003/06/13
· · · ·		gan) and Qad<20010305) and 438/\$3.ccls.	US-PGPUB;	21:09
. (		gair, and gau\20010303) and 430/73.CCIS.		21.05
}			EPO; JPO;	1
}	()		DERWENT	,
<b>]</b> -	140582	(substrate with sapphire or (silicon adj	USPAT;	2004/05/04
	1	carbide) or "al.sub.2o.sub.3" or "sic")	US-PGPUB;	15:43
1	. 1		EPO; JPO;	
	1		DERWENT	
}	i		י ווו אינוער אוער און ו	1

	- 4	·				·
			2080	(buffer with (over or on) with substrate)	USPAT;	2004/05/04
- {	•				US-PGPUB;	15:44
- {			•		EPO; JPO;	
-{					DERWENT	
- [	<u>.</u> .		1190	((semiconductor or "gan") with (on or	USPAT;	2004/05/04
- [				over) with buffer)	US-PGPUB;	15:45
. }	٠.			Over, with buller,	EPO; JPO;	13.43
1			<b>)</b>		,	
1			470006	(/	DERWENT	2004:/05 /04
1	<b>-</b> ·		418296	((remov\$3 or thin\$4 etch\$3) with	USPAT;	2004/05/04
			}	substrate) :	US-PGPUB;	15:45
-{	•	• •			EPO; JPO;	
- (					DERWENT	
- (	- ' .	·	295	((substrate with sapphire or (silicon adj	USPAT;	2004/05/04
[				carbide) or "al.sub.20.sub.3" or "sic"))	US-PGPUB;	15:46
ļ	. ,			and ((buffer with (over or on) with	EPO; JPO;	
- }			. *			
┧				substrate)) and (((semiconductor or	DERWENT	
- {	•	٠,	·	"gan") with (on or over) with buffer))		
┪		,	<u> </u>	and (((remov\$3 or thin\$4 etch\$3) with		( )
ł	£		·	substrate))	•	
,	<b>-</b> ,	•	12	((substrate with sapphire or (silicon adj	USPAT;	2004/05/04
, {		1		carbide) or "al.sub.20.sub.3" or "sic"))	US-PGPUB;	15:48
1	.:	, 1		same ((buffer with (over or on) with	EPO; JPO;	h h h
1	•		)	substrate)) same (((semiconductor or	DERWENT	
1		i	]	"gan") with (on or over) with buffer))	PHIMINT	}
			·		0	
1				same (((remov\$3 or thin\$4 etch\$3) with		
ł	•	,	_ `	substrate))	·	000440540
	<del>-</del> '.	,	8.7	(((substrate with sapphire or (silicon	USPAT;	2004/05/04
- [			• 4	adj carbide) or "al.sub.20.sub.3" or	US-PGPUB;	15:59
- [	•			"sic")) same ((buffer with (over or on)	EPO; JPO;	
		r_		with substrate)) same (((semiconductor or	DERWENT	
- }	. •			"gan") with (on or over) with buffer))	• •	
- }				same (((remov\$3 or thin\$4 etch\$3) with	<i>.</i> .	
ł	•		-8-	substrate))) and (@ad<20010305.or		
ł				@rlad<20010305)		
1	_	•	. 55	(((substrate with sapphire or (silicon	USPAT;	2004/05/04
.	•			adj carbide) or "al.sub.20.sub.3" or	US-PGPUB;	15:59
-[	٠.	*			· ·	13.39
Į.		;		"sic")) and ((buffer with (over or on)	EPO; JPO;	
, [				with substrate)) and (((semiconductor or	DERWENT	
.		f		"gan") with (on or over) with buffer))		
┨			, '	and (((remov\$3 or thin\$4 etch\$3) with		
┪				substrate))) and (second with buffer with	, .	
1		,		(semiconductor or "gan"))	_	
1	<u></u> *		30	((((substrate with sapphire or (silicon	USPAT;	2004/05/04
1				adj carbide) or "al.sub.2o.sub.3" or	US-PGPUB;	17:27
1				"sic")) and ((buffer with (over or on)	EPO; JPO;	
1	:.•			with substrate)) and (((semiconductor or	DERWENT	
1	٠, ٠			"gan") with (on or over) with buffer))		
ţ			, (	and (((remov\$3 or thin\$4 etch\$3) with	,	
- [					•	. ∞
.	• • • •			substrate))) and (second with buffer with	•	
		٠		(semiconductor or "gan"))) and	•	· •
- {			, ,	(@ad<20010305 or @rlad<20010305)		0004/05/05
1	<del>-</del> .	:	1	form\$3 with buffer with stress with base	USPAT;	2004/05/04
1	* <sub>4</sub> 1 <sub>6</sub>	•		with main with substrate	US-PGPUB;	17:25
`{	٠				EPO; JPO;	
ſ					DERWENT	_ `
1	·	• '.	115	form\$3 with buffer with stress with	USPAT;	2004/05/04
1				(semiconductor or "gan") with (substrate	US-PGPUB;	17:26
1	15.5			or sapphire or (silicon adj carbide) or	EPO; JPO;	
- [				"al.sub.2o.sub.3" or "sic")	DERWENT	
. [	_		51	(form\$3 with buffer with stress with	USPAT;	2004/05/04
-				(semiconductor or "gan") with (substrate	US-PGPUB;	17:27
. }	•		·[	or sapphire or (silicon adj carbide) or		17.27
}			, }		EPO; JPO;	, , ,
.				"al.sub.2o.sub.3" or "sic")) and (second	DERWENT	
ł	•	·		with buffer)	****	0005/05/05
1			36	((form\$3 with buffer with stress with	USPAT;	2004/05/04
1		. )		(semiconductor or "gan") with (substrate	US-PGPUB;	19:21
Į		` ]		or sapphire or (silicon adj carbide) or	EPO; JPO;	• • • • • • •
1		į	• [	"al.sub.20.sub.3" or "sic")) and (second	DERWENT	·
- {		(	-[	with buffer)) and (@ad<20010305 or		
1			;	@rlad<20010305)	•	
_						

<b>-</b>	157	((form\$3 with buffer with (over or on) with (semiconductor or "gan") with (substrate or sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and (second with buffer)) and	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 19:58
· · · · · · · · · · · · · · · · · · ·	75	(@ad<20010305 or @rlad<20010305) (((form\$3 with buffer with (over or on) with (semiconductor or "gan") with (substrate or sapphire or (silicon adj carbide) or "al.sub.20.sub.3" or "sic")) and (second with buffer)) and	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 19:23
	68	(cad<20010305 or @rlad<20010305)) and (remov\$3 with (substrate or sapphire or (silicon adj carbide) or "al.sub.20.sub.3" or "sic"))		40
		(form\$3 with buffer with (over or on) with "gan") and (@ad<20010305 or @rlad<20010305)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 19:59